

RGTH60TK65

650V 30A Field Stop Trench IGBT

V _{CES}	650V
I _{C(100°C)}	17A
V _{CE(sat) (Typ.)}	1.6V@I _C =30A
P_D	61W

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Pb free Lead Plating; RoHS Compliant

Applications

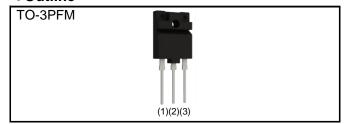
PFC

UPS

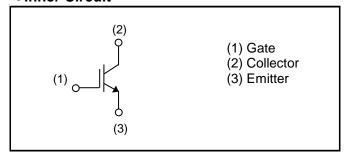
Power Conditioner

ΙH

Outline



●Inner Circuit



Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Tuno	Tape Width (mm)	-
Type	Basic Ordering Unit (pcs)	450
	Packing Code	C11
	Marking	RGTH60TK65

● Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V_{CES}	650	V
Gate - Emitter Voltage		V_{GES}	±30	V
Collector Current	T _C = 25°C	I _C	28	А
	T _C = 100°C	I _C	17	А
Pulsed Collector Current		I _{CP} *1	120	А
Power Dissipation	T _C = 25°C	P_{D}	61	W
	T _C = 100°C	P _D	30	W
Operating Junction Temperature		T _j	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

^{*1} Pulse width limited by T_{jmax.}

●Thermal Resistance

Darameter	Symbol	Values			Unit
Parameter		Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	2.43	°C/W

ullet IGBT Electrical Characteristics (at $T_j = 25$ °C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
raiainetei	dei Symbol Conditions		Min.	Тур.	Max.	Unit
Collector - Emitter Breakdown Voltage	BV _{CES}	$I_{C} = 10 \mu A, V_{GE} = 0 V$	650	ı	1	V
Collector Cut - off Current	I _{CES}	$V_{CE} = 650V, V_{GE} = 0V$	1	1	10	μΑ
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30V$, $V_{CE} = 0V$		-	±200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5V, I_{C} = 21.0 \text{mA}$	4.5	5.5	6.5	V
Collector - Emitter Saturation Voltage	V _{CE(sat)}	$I_C = 30A$, $V_{GE} = 15V$ $T_j = 25$ °C $T_j = 175$ °C	-	1.6 2.1	2.1 -	V

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Dorometer	Cumbal	Conditions	Values			l lmit
Parameter	Symbol		Min.	Тур.	Max.	Unit
Input Capacitance	C _{ies}	V _{CE} = 30V	-	1670	-	
Output Capacitance	C _{oes}	$V_{GE} = 0V$	-	66	-	pF
Reverse Transfer Capacitance	C _{res}	f = 1MHz	-	27	-	
Total Gate Charge	Q_g	V _{CE} = 300V	-	58	-	
Gate - Emitter Charge	Q_ge	I _C = 30A	-	15	-	nC
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	20	-	
Turn - on Delay Time	t _{d(on)}	$I_C = 30A, V_{CC} = 400V$	-	27	-	
Rise Time	t _r	$V_{GE} = 15V, R_G = 10\Omega$	-	40	-	
Turn - off Delay Time	t _{d(off)}	T _j = 25°C	-	105	-	ns
Fall Time	t _f	Inductive Load	-	47	-	
Turn - on Delay Time	t _{d(on)}	$I_C = 30A, V_{CC} = 400V$	-	27	-	
Rise Time	t _r	$V_{GE} = 15V, R_G = 10\Omega$	-	40	-	
Turn - off Delay Time	$t_{d(off)}$	T _j = 175°C	-	120	-	ns
Fall Time	t _f	Inductive Load	-	59	-	
		I _C = 120A, V _{CC} = 520V		-		
Reverse Bias Safe Operating Area	RBSOA	$V_P = 650 \text{V}, V_{GE} = 15 \text{V}$	FULL SQUARE			-
		$R_G = 60\Omega, T_j = 175^{\circ}C$				

• Electrical Characteristic Curves

Fig.1 Power Dissipation vs. Case Temperature

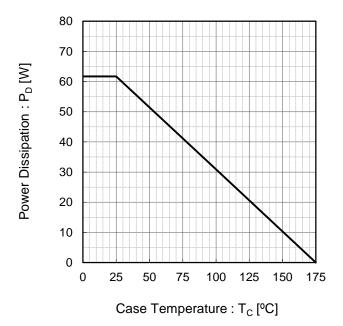


Fig.2 Collector Current vs. Case Temperature

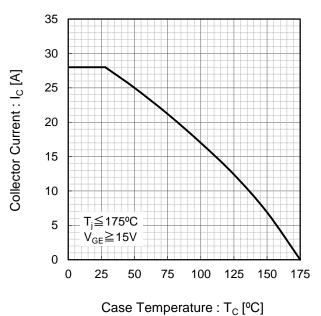


Fig.3 Forward Bias Safe Operating Area

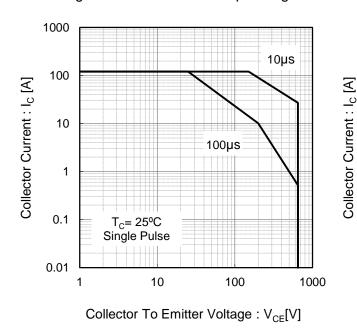
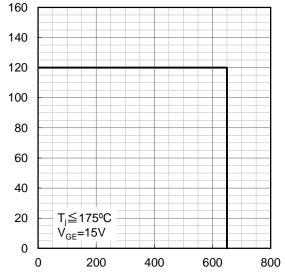


Fig.4 Reverse Bias Safe Operating Area



Collector To Emitter Voltage : $V_{CE}[V]$

•Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

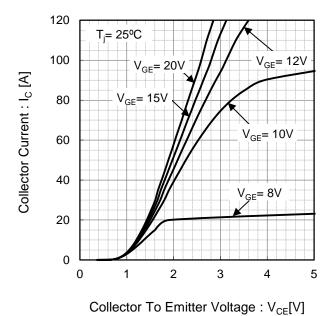
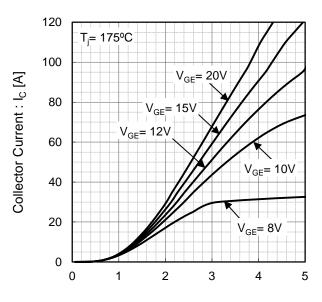


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage : V_{CE}[V]

Fig.7 Typical Transfer Characteristics

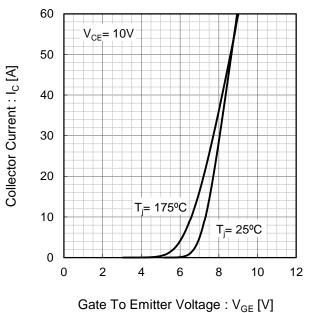
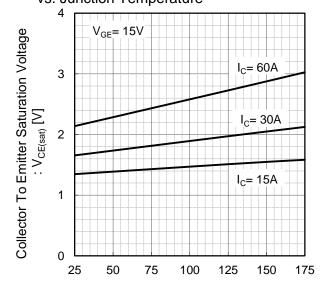


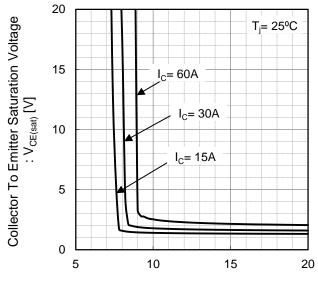
Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



Junction Temperature : T_i [°C]

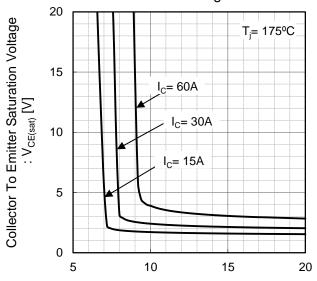
•Electrical Characteristic Curves

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage : V_{GE} [V]

Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage: V_{GE} [V]

Fig.11 Typical Switching Time vs. Collector Current

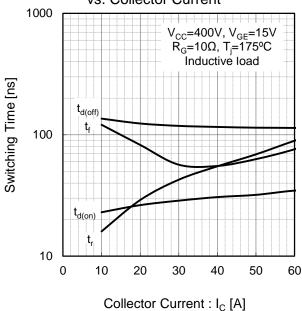
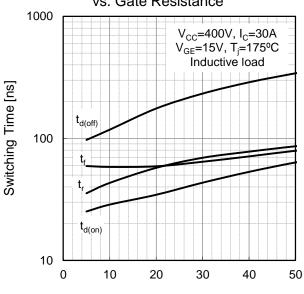


Fig.12 Typical Switching Time vs. Gate Resistance



• Electrical Characteristic Curves

Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] 1 0.1 $V_{\rm CC}$ =400V, $V_{\rm GE}$ =15V R_G=10 Ω , T_j=175°C Inductive load 0.01 0 40 50 10 20 30 60 Collector Current : I_C [A]

vs. Gate Resistance

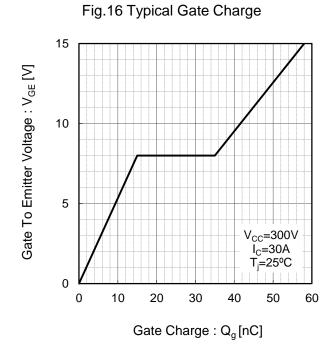
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See Section 1

Eoff $V_{cc} = 400V, I_{c} = 30A$ $V_{GE} = 15V, T_{J} = 175^{\circ}C$ Inductive load $V_{cc} = 400V, I_{c} = 30A$ $V_{GE} = 15V, T_{J} = 175^{\circ}C$ $V_{CC} = 400V, I_{C} = 30A$ $V_{GE} = 15V, T_{J} = 175^{\circ}C$ $V_{CC} = 400V, I_{C} = 30A$ $V_{CC} = 40V, I_{C} = 30A$

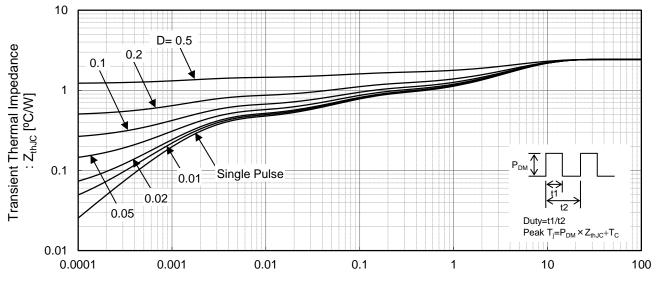
Fig.14 Typical Switching Energy Losses

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] Coes 100 Cres 10 f=1MHz $V_{GE}=0V$ T_i=25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage : V_{CE}[V]



•Electrical Characteristic Curves

Fig.17 IGBT Transient Thermal Impedance



●Inductive Load Switching Circuit and Waveform

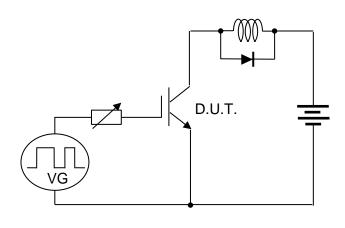


Fig.18 Inductive Load Circuit

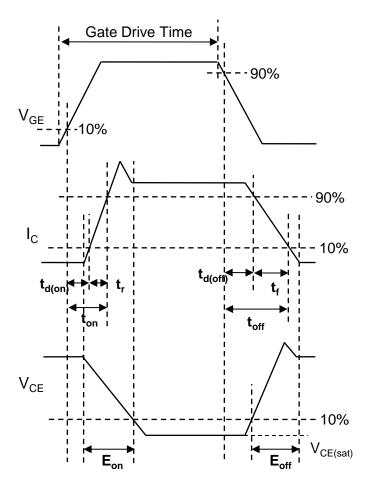


Fig.19 Inductive Load Waveform

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